SM74104 High Voltage Half-Bridge Gate Driver with Adaptive Delay

1 Features

- Renewable Energy Grade
- Drives both a High Side and Low Side N-Channel MOSFET
- Adaptive Rising and Falling Edges with Programmable Additional Delay
- Single Input Control
- Bootstrap Supply Voltage Range up to 118V DC
- Fast Turn-Off Propagation Delay (25 ns Typical)
- Drives 1000 pF Loads with 15 ns Rise and Fall Times
- Supply Rail Under-Voltage Lockout

2 Typical Applications

- Current Fed Push-Pull Power Converters
- High Voltage Buck Regulators
- Active Clamp Forward Power Converters
- Half and Full Bridge Converters

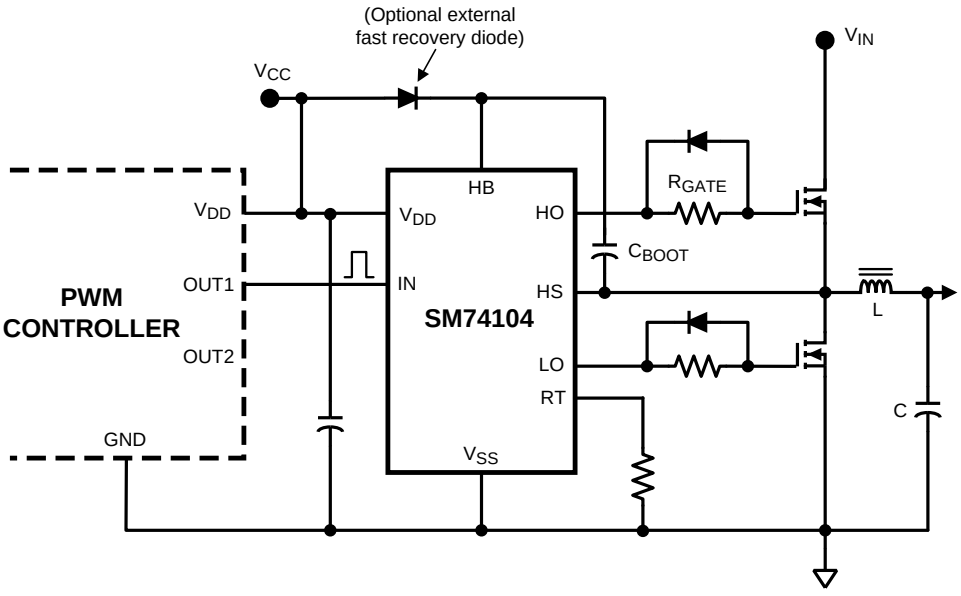
3 Description

The SM74104 High Voltage Gate Driver is designed to drive both the high side and the low side N-Channel MOSFETs in a synchronous buck configuration. The floating high-side driver is capable of working with supply voltages up to 100V. The high side and low side gate drivers are controlled from a single input. Each change in state is controlled in an adaptive manner to prevent shoot-through issues. In addition to the adaptive transition timing, an additional delay time can be added, proportional to an external setting resistor. An integrated high voltage diode is provided to charge the high side gate drive bootstrap capacitor. A robust level shifter operates at high speed while consuming low power and providing clean level transitions from the control logic to the high side gate driver. Under-voltage lockout is provided on both the low side and the high side power rails.

Device Information(1)

PART NUMBER	PACKAGE	BODY SIZE (NOM)
SM74104	WSON (10)	4.0 mm x 4.0 mm
	SOIC (8)	4.9 mm x 3.9 mm

(1) For all available packages, see the orderable addendum at the end of the data sheet.



SM74104 Driving MOSFETs Connected in Synchronous Buck Configuration

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4 Revision History

NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

Changes from Revision C (April 2013) to Revision D **Page**

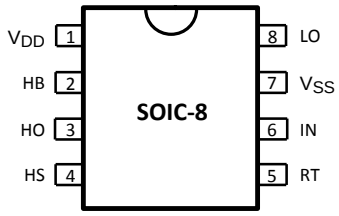
- Added *ESD Ratings* table, *Thermal Information* table, *Feature Description* section, *Device Functional Modes*, *Application and Implementation* section, *Power Supply Recommendations* section, *Layout* section, *Device and Documentation Support* section, and *Mechanical, Packaging, and Orderable Information* section ... 1

Changes from Revision B (April 2013) to Revision C **Page**

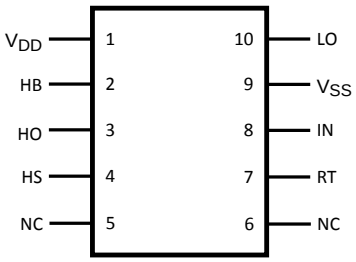
- Changed layout of National Data Sheet to TI format ... 1

5 Pin Configuration and Functions

8-Pin SOIC
Package D
Top View



10-Pin WSON
Package DPR
Top View



Pin Functions

PIN			I/O	DESCRIPTION
NAME	NO.			
	D	DPR		
VDD	1	1	I	Positive supply voltage input.
HB	2	2	I	Positive connection for high-side bootstrap capacitor.
HO	3	3	O	High-side output to drive the top MOSFET.
HS	4	4	I	Switch node pin.
RT	5	7	I	Delay timer pin. The additional delay of the timer prevents lower and upper MOSFETs from conducting simultaneously, thereby preventing shoot-through. Timer delay is set with a resistor to ground.
IN	6	8	I	PWM control input for LO and HO outputs.
VSS	7	9	-	Ground pin.
LO	8	10	O	Low-side output to drive the bottom MOSFET.
N/C	-	5, 6	-	No connect.
Exposed Pad	-	Exposed Pad	-	The exposed die attach pad (DAP) on the 10-pin WSON package functions as a thermal connection and can be soldered to a copper plane under the device. The DAP nas no direct electrical connection to any of the pins. It can be left floating, but it is recommended to connect this to V_{SS}.

6 Specifications

7 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted) (1)

	MIN	MAX	UNIT
V_{DD} to V_{SS}	–0.3	18	V
V_{HB} to V_{HS}	–0.3	18	V
IN to V_{SS}	–0.3	V_{DD} + 0.3	V
LO Output	–0.3	V_{DD} + 0.3	V
HO Output	V_{HS} – 0.3	V_{HB} + 0.3	V
V_{HS} to V_{SS}	–1	100	V
V_{HB} to V_{SS}		118	V
RT to V_{SS}	–0.3	5	V
T_{stg} Storage Temperature Range	–55	150	°C
Maximum Junction Temperature		150	°C

(1) Stresses beyond those listed under *Absolute Maximum Ratings* may cause permanent damage to the device. These are stress ratings only, which do not imply functional operation of the device at these or any other conditions beyond those indicated under *Recommended Operating Conditions*. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

8 ESD Ratings

				VALUE	UNIT
$V_{(ESD)}$	Electrostatic discharge	Human-body model (HBM), per ANSI/ESDA/JEDEC JS-001 (1)	All pins except 2, 3, and 4	±2000	V
			Pins 2, 3, and 4	±500	

(1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process. Manufacturing with less than 500-V HBM is possible with the necessary precautions.

9 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)

	MIN	MAX	UNIT
V_{DD}	9	14	V
HS	–1	100	V
HB	V_{HS} + 8	V_{HS} + 14	V
HS Slew Rate		50	V/ns
Junction Temperature	–40	125	°C

10 Thermal Information

THERMAL METRIC (1)		SM74104		UNIT
		D	DPR	
		8 PINS	10 PINS	
$R_{\theta JA}$	Junction-to-ambient thermal resistance	114.5	37.9	°C/W
$R_{\theta JC(top)}$	Junction-to-case (top) thermal resistance	61.1	38.1	
$R_{\theta JB}$	Junction-to-board thermal resistance	55.6	14.9	
ψ_{JT}	Junction-to-top characterization parameter	9.7	0.4	
ψ_{JB}	Junction-to-board characterization parameter	54.9	15.2	
$R_{\theta JC(bot)}$	Junction-to-case (bottom) thermal resistance	-	4.4	

(1) For more information about traditional and new thermal metrics, see the *IC Package Thermal Metrics* application report, SPRA953.

11 Electrical Characteristics

Over operating junction temperature range, V_{DD} = V_{HB} = 12 V, V_{SS} = V_{HS} = 0 V, RT = 100 kΩ, no load on LO or HO, unless otherwise specified.

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
SUPPLY CURRENTS						
I_{DD}	V_{DD} Quiescent Current	LI = HI = 0V		0.4	0.6	mA
I_{DDO}	V_{DD} Operating Current	f = 500 kHz		1.9	3	mA
I_{HB}	Total HB Quiescent Current	LI = HI = 0V		0.06	0.2	mA
I_{HBO}	Total HB Operating Current	f = 500 kHz		1.3	3	mA
I_{HBS}	HB to V_{SS} Current, Quiescent	V_{HS} = V_{HB} = 100V		0.05	10	µA
I_{HBSO}	HB to V_{SS} Current, Operating	f = 500 kHz		0.08		mA
INPUT PINS						
V_{IL}	Low Level Input Voltage Threshold		0.8	1.8		V
V_{IH}	High Level Input Voltage Threshold			1.8	2.2	V
R_I	Input Pulldown Resistance		100	200	500	kΩ
TIME DELAY CONTROLS						
V_{RT}	Nominal Voltage at RT		2.7	3	3.3	V
I_{RT}	RT Pin Current Limit	RT = 0V	0.75	1.5	2.25	mA
T_{D1}	Delay Timer, RT = 10 kΩ		58	90	130	ns
T_{D2}	Delay Timer, RT = 100 kΩ		140	200	270	ns
UNDER VOLTAGE PROTECTION						
V_{DDR}	V_{DD} Rising Threshold		6.0	6.9	7.4	V
V_{DDH}	V_{DD} Threshold Hysteresis			0.5		V
V_{HBR}	HB Rising Threshold		5.7	6.6	7.1	V
V_{HBH}	HB Threshold Hysteresis			0.4		V
BOOT STRAP DIODE						
V_{DL}	Low-Current Forward Voltage	I_{VDD-HB} = 100 µA		0.60	0.9	V
V_{DH}	High-Current Forward Voltage	I_{VDD-HB} = 100 mA		0.85	1.1	V
R_D	Dynamic Resistance	I_{VDD-HB} = 100 mA		0.8	1.5	Ω
LO GATE DRIVER						
V_{OLL}	Low-Level Output Voltage	I_{LO} = 100 mA		0.25	0.4	V
V_{OHL}	High-Level Output Voltage	I_{LO} = –100 mA V_{OHL} = V_{DD} – V_{LO}		0.35	0.55	V
I_{OHL}	Peak Pullup Current	V_{LO} = 0V		1.6		A
I_{OLL}	Peak Pulldown Current	V_{LO} = 12V		1.8		A
HO GATE DRIVER						
V_{OLH}	Low-Level Output Voltage	I_{HO} = 100 mA		0.25	0.4	V
V_{OHH}	High-Level Output Voltage	I_{HO} = –100 mA, V_{OHH} = V_{HB} – V_{HO}		0.35	0.55	V
I_{OHH}	Peak Pullup Current	V_{HO} = 0V		1.6		A
I_{OLH}	Peak Pulldown Current	V_{HO} = 12V		1.8		A

12 Switching Characteristics

Over operating junction temperature range, $V_{DD} = V_{HB} = 12$ V, $V_{SS} = V_{HS} = 0$ V, no load on LO or HO, unless otherwise specified.

Symbol	Parameter	Conditions	Min	Typ	Max	Units
t_{LPHL}	Lower Turn-Off Propagation Delay (IN Rising to LO Falling)			25	56	ns
t_{HPHL}	Upper Turn-Off Propagation Delay (IN Falling to HO Falling)			25	56	ns
t_{RC}, t_{FC}	Either Output Rise/Fall Time	C_L = 1000 pF		15		ns
t_R, t_F	Either Output Rise/Fall Time (3V to 9V)	C_L = 0.1 µF		0.6		µs
t_{BS}	Bootstrap Diode Turn-Off Time	I_F = 20 mA, I_R = 200 mA		50		ns

12.1 Typical Performance Characteristics

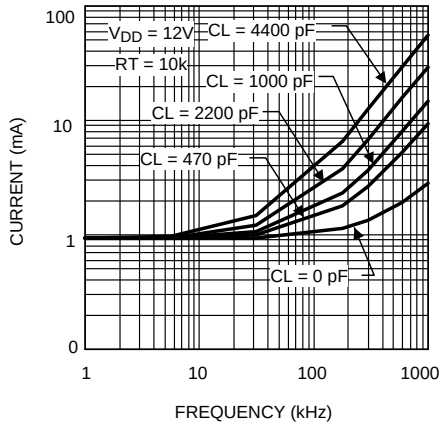


Figure 1. I_{DD} vs Frequency

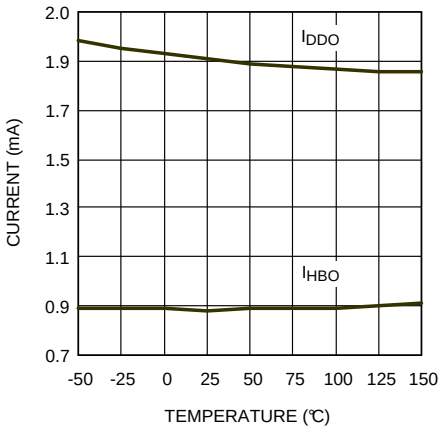


Figure 2. Operating Current vs Temperature

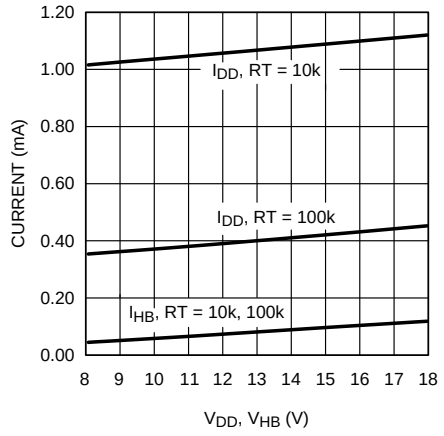


Figure 3. Quiescent Current vs Supply Voltage

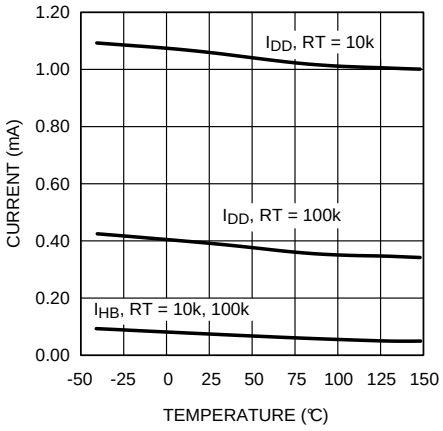


Figure 4. Quiescent Current vs Temperature

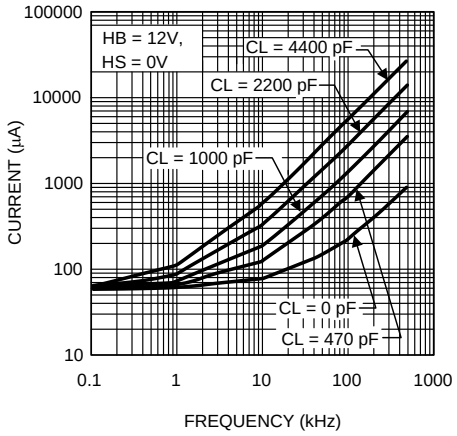


Figure 5. I_{HB} vs Frequency

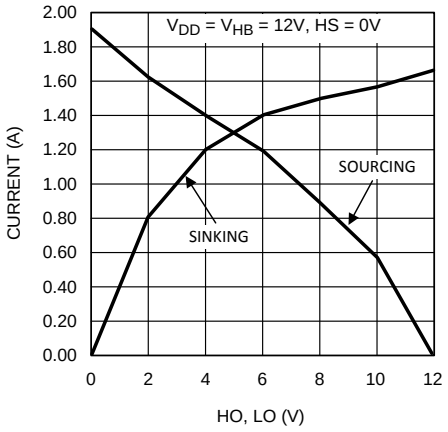


Figure 6. HO & LO Peak Output Current vs Output Voltage

Typical Performance Characteristics (continued)

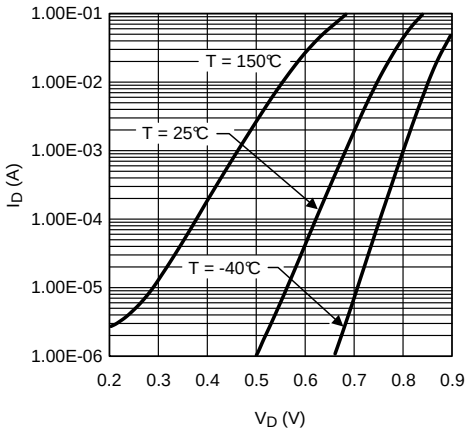


Figure 7. Diode Forward Voltage

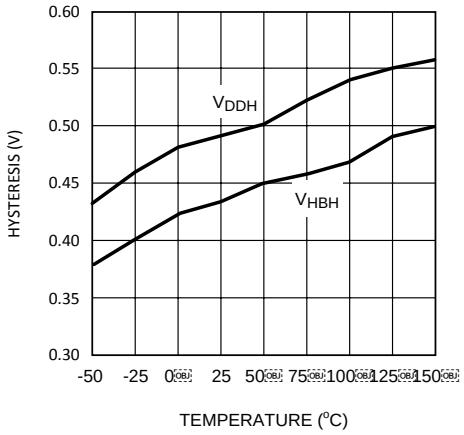


Figure 8. Undervoltage Threshold Hysteresis vs Temperature

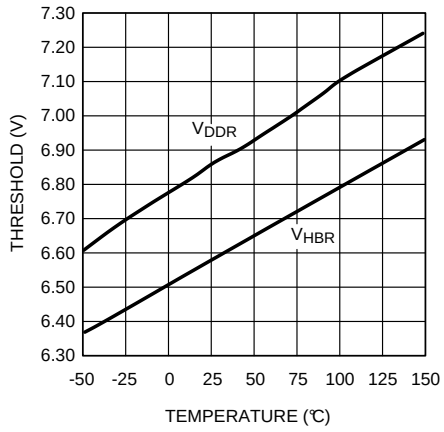


Figure 9. Undervoltage Rising Threshold vs Temperature

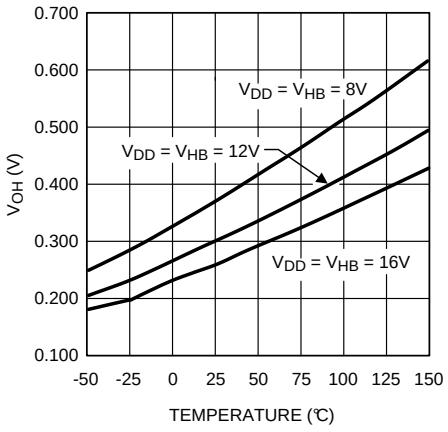


Figure 10. LO & HO Gate Drive—High Level Output Voltage vs Temperature

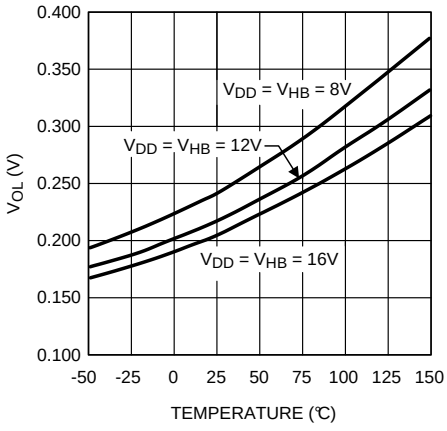


Figure 11. LO & HO Gate Drive—Low Level Output Voltage vs Temperature

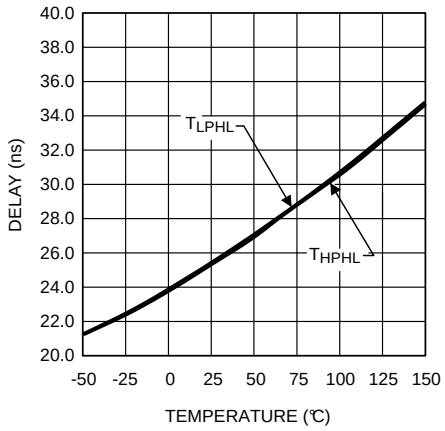


Figure 12. Turn Off Propagation Delay vs Temperature

Typical Performance Characteristics (continued)

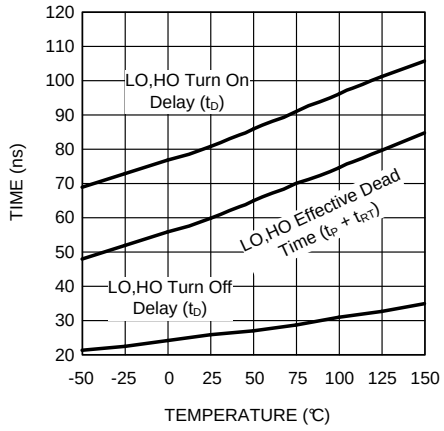


Figure 13. Timing vs Temperature RT = 10K

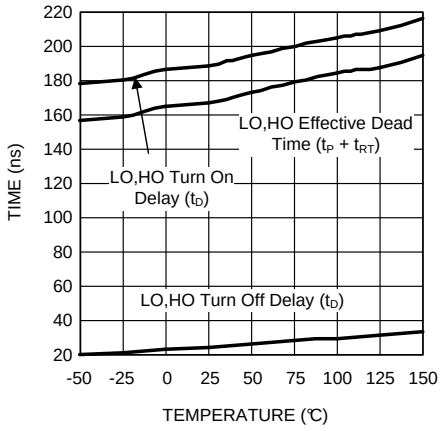


Figure 14. Timing vs Temperature RT = 100K

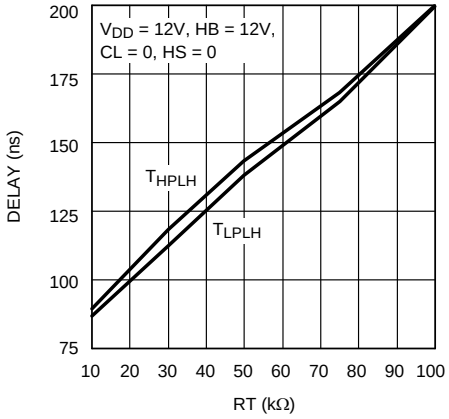


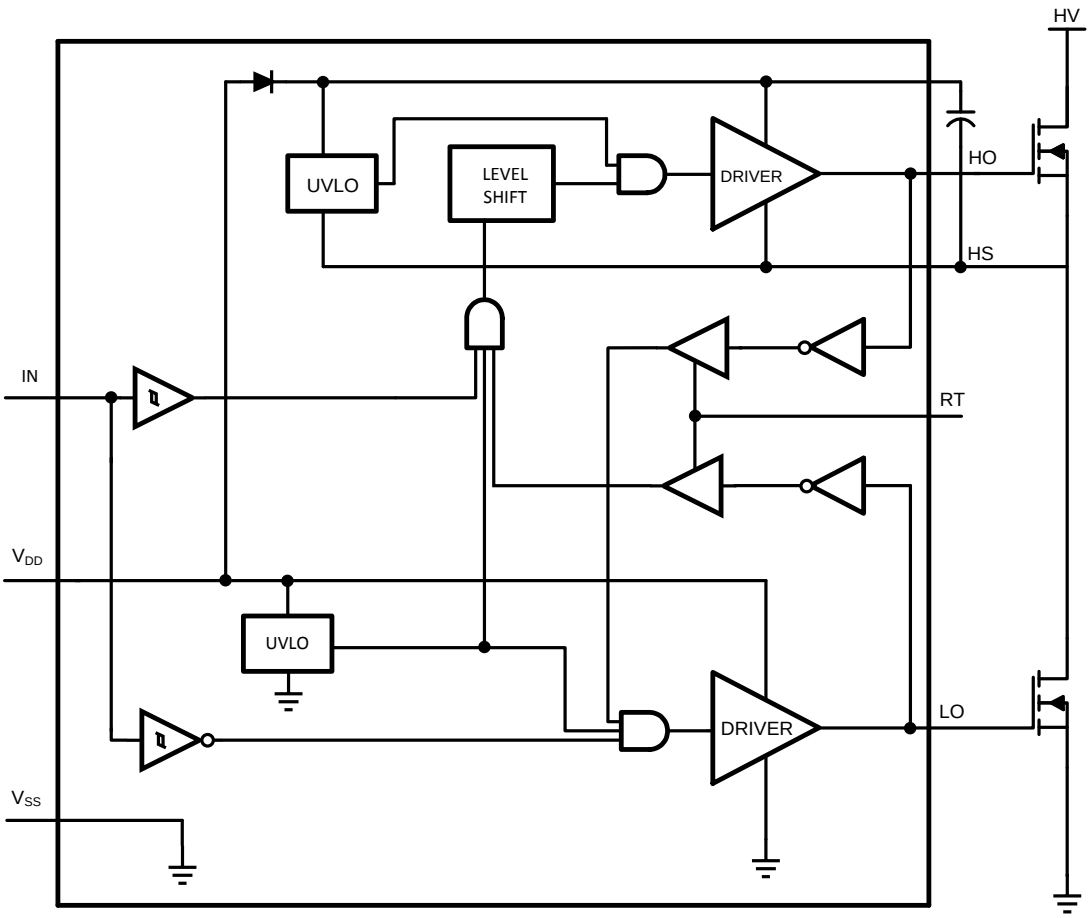
Figure 15. Turn On Delay vs RT Resistor Value

13 Detailed Description

13.1 Overview

SM74104 is a high voltage, high speed, dual output driver designed to drive top and bottom MOSFETs connected in synchronous buck or half-bridge configuration. SM74104 also features adaptive delay to prevent shoot-through current through top and bottom MOSFETs during switching transitions. The outputs that drive the top and bottom MOSFETs are controlled by one externally provided PWM signal.

13.2 Functional Block Diagram



13.3 Feature Description

13.3.1 PWM Input Control

Referring to the timing diagram in Figure 16, the rising edge of the PWM input (IN) turns off the bottom MOSFET (LO) after a short propagation delay (t_P). An adaptive circuit in the SM74104 monitors the bottom gate voltage (LO) and triggers a programmable delay generator when the LO pin falls below an internally set threshold (≈ Vdd/2). The gate drive of the upper MOSFET (HO) is disabled until the deadtime expires. The upper gate is enabled after the TIMER delay (t_P+T_{RT}), and the upper MOSFET turns-on. The additional delay of the timer prevents lower and upper MOSFETs from conducting simultaneously, thereby preventing shoot-through.

Feature Description (continued)

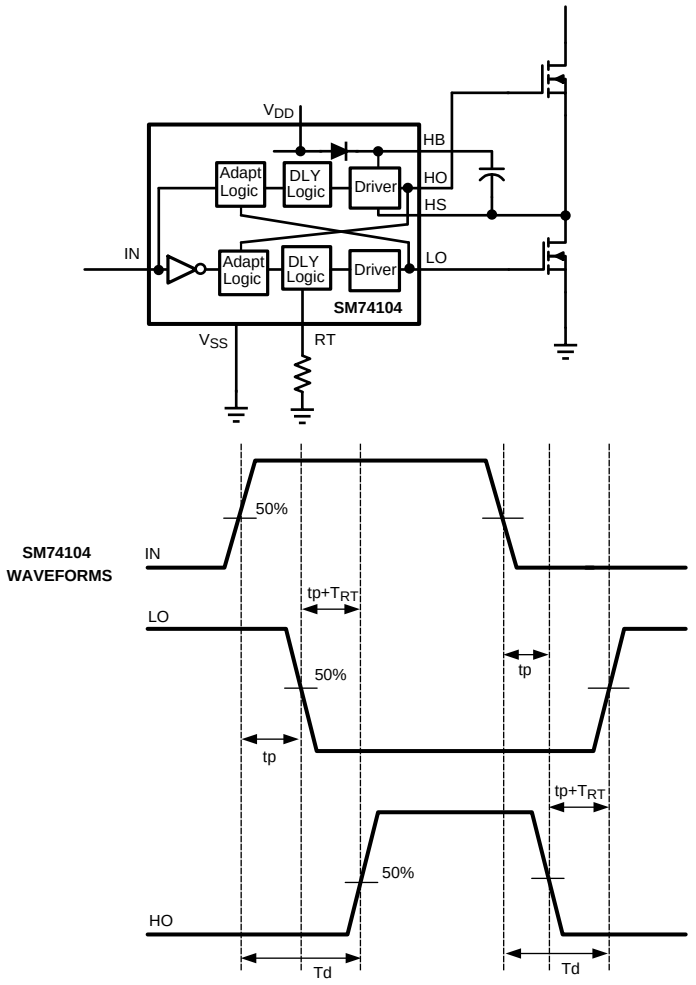


Figure 16. Application Timing Waveforms

A falling transition on the PWM signal (IN) initiates the turn-off of the upper MOSFET and turn-on of the lower MOSFET. A short propagation delay (t_P) is encountered before the upper gate voltage begins to fall. Again, the adaptive shoot-through circuitry and the programmable deadtime TIMER delays the lower gate turn-on time. The upper MOSFET gate voltage is monitored and the deadtime delay generator is triggered when the upper MOSFET gate voltage with respect to ground drops below an internally set threshold (≈ Vdd/2). The lower gate drive is momentarily disabled by the timer and turns on the lower MOSFET after the deadtime delay expires (t_P+T_{RT}).

13.3.2 Setting the Delay Timer with RT

The RT pin is biased at 3V and current limited to 1mA. It is designed to accommodate a resistor between 5K and 100K, resulting in an effective dead-time proportional to RT and ranging from 90ns to 200ns. RT values below 5K will saturate the timer and are not recommended.

13.4 Device Functional Modes

13.4.1 Startup and UVLO

Both top and bottom drivers include under-voltage lockout (UVLO) protection circuitry which monitors the supply voltage (V_{DD}) and bootstrap capacitor voltage ($V_{HB} – V_{HS}$) independently. The UVLO circuit inhibits each driver until sufficient supply voltage is available to turn-on the external MOSFETs, and the built-in hysteresis prevents chattering during supply voltage transitions. When the supply voltage is applied to V_{DD} pin of SM74104, the top and bottom gates are held low until V_{DD} exceeds UVLO threshold, typically about 6.9V. Any UVLO condition on the bootstrap capacitor will disable only the high side output (HO).

13.5 Power Dissipation Considerations

The total IC power dissipation is the sum of the gate driver losses and the bootstrap diode losses. The gate driver losses are related to the switching frequency (f), output load capacitance on LO and HO (C_L), and supply voltage (V_{DD}) and can be roughly calculated as:

$$P_{DGATES} = 2 \bullet f \bullet C_L \bullet V_{DD}^2 \quad (1)$$

There are some additional losses in the gate drivers due to the internal CMOS stages used to buffer the LO and HO outputs. The following plot shows the measured gate driver power dissipation versus frequency and load capacitance. At higher frequencies and load capacitance values, the power dissipation is dominated by the power losses driving the output loads and agrees well with the above equation. This plot can be used to approximate the power losses due to the gate drivers.

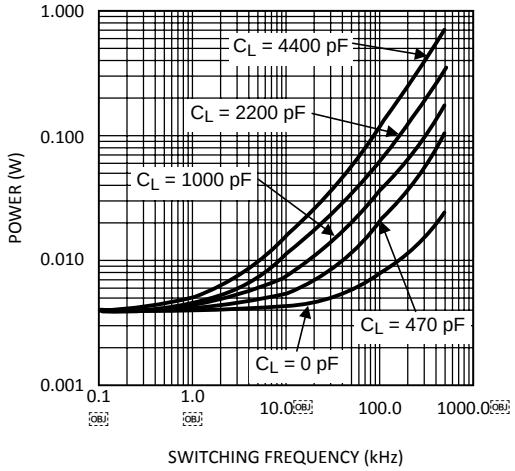


Figure 17. Gate Driver Power Dissipation (LO + HO)
V_{CC} = 12V, Neglecting Diode Losses

The bootstrap diode power loss is the sum of the forward bias power loss that occurs while charging the bootstrap capacitor and the reverse bias power loss that occurs during reverse recovery. Since each of these events happens once per cycle, the diode power loss is proportional to frequency. Larger capacitive loads require more current to recharge the bootstrap capacitor resulting in more losses. Higher input voltages (V_{IN}) to the half bridge result in higher reverse recovery losses. The following plot was generated based on calculations and lab measurements of the diode recovery time and current under several operating conditions. This can be useful for approximating the diode power dissipation.

Power Dissipation Considerations (continued)

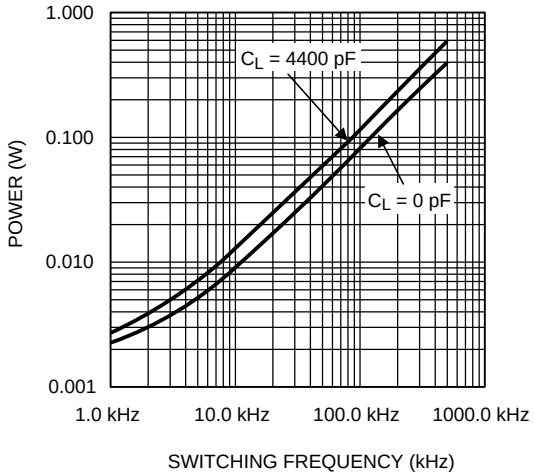


Figure 18. Diode Power Dissipation V_{IN} = 80V

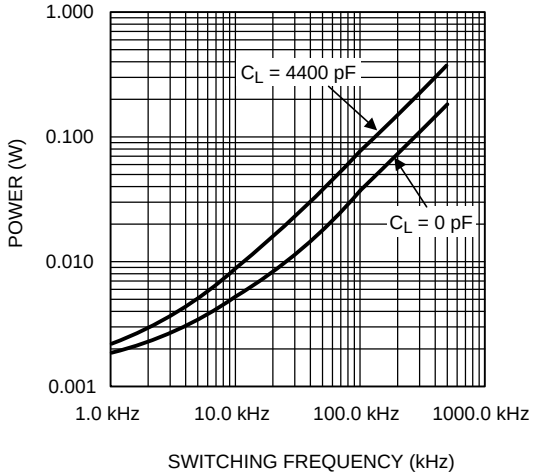


Figure 19. Diode Power Dissipation V_{IN} = 40V

The total IC power dissipation can be estimated from the above plots by summing the gate drive losses with the bootstrap diode losses for the intended application. Because the diode losses can be significant, an external diode placed in parallel with the internal bootstrap diode (refer to Figure 20) can be helpful in removing power from the IC. For this to be effective, the external diode must be placed close to the IC to minimize series inductance and have a significantly lower forward voltage drop than the internal diode.

14 Application and Implementation

NOTE

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes. Customers should validate and test their design implementation to confirm system functionality.

14.1 Application Information

The SM74104 can drive both a high-side and a low-side MOSFET using only one PWM input control signal. The internal level shifter provides a means for the control input to drive the high-side MOSFET. The SM74104 prevents shoot-through issues through adaptive transition timing and an additional time delay can be added by use of an external resistor at the RT pin.

14.2 Typical Application

The SM74104 is used to drive MOSFETs connected in a synchronous buck configuration as shown in Figure 20. A single control signal from an external PWM controller provides the control input to drive both the high-side and low-side MOSFET. The HO and LO outputs of the SM74104 can provide very fast switching of the MOSFETs, thereby reducing switching losses and improving the overall efficiency of the system.

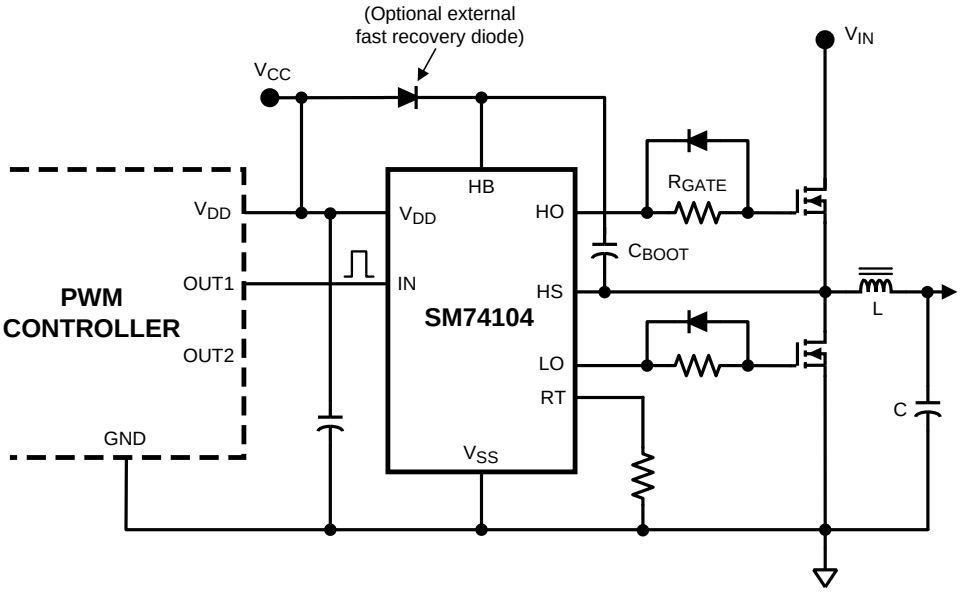


Figure 20. Typical Application

14.2.1 Design Requirements

The RT resistor should be sized such that the appropriate time delay is added between the switching transitions of the top and bottom MOSFETs. The exact RT value will depend on the selected MOSFETs, their switching speeds, and the desired delay time needed to prevent shoot-through. An optional external fast recovery diode should be placed between the VDD and HB pins to minimize the stress on the internal bootstrap diode and decrease the average power dissipation in the IC. An R_{GATE} resistor and a parallel diode may also be placed in the path of the MOSFET gates. The R_{GATE} resistor will decrease the ON switching speed of the MOSFET and can help damp possible oscillations on the line. The parallel diode will provide a current path around R_{GATE} during the OFF switching of the MOSFET, which can ensure fast shut off of the MOSFET to further prevent shoot-through.

Typical Application (continued)

14.2.2 Detailed Design Procedure

See Power Supply Recommendations, Layout, and Power Dissipation Considerations for key design considerations regarding the input supply, grounding, component placement, and power calculations specific to the SM74104.

14.2.3 Application Curve

An adaptive circuit in the SM74104 monitors the gate voltages of the top and bottom MOSFETs and triggers a programmable delay generator to prevent both MOSFETs from conducting simultaneously. The timer delay, T_{RT}, can be programmed with a resistor placed between RT and VSS. The value of T_{RT} will vary with the RT resistor value as shown in Figure 21.

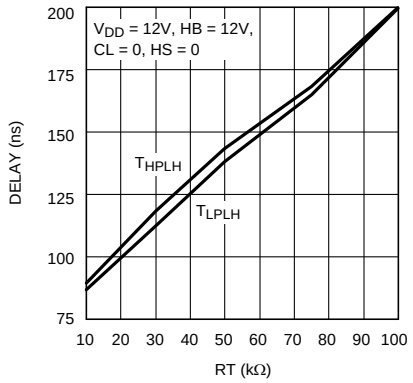


Figure 21. Turn On Delay vs RT Resistor Value

15 Power Supply Recommendations

A low ESR/ESL capacitor must be connected as close as possible to the IC between V_{DD} and V_{SS} pins and between HB and HS pins to support high peak currents being drawn from V_{DD} during turn-on of the external MOSFET. Also, to prevent large voltage transients at the drain of the top MOSFET, a low ESR electrolytic capacitor must be connected between MOSFET drain and ground (V_{SS}). In both cases, the traces should be as short as possible to reduce the series resistance.

16 Layout

16.1 Layout Guidelines

The optimum performance of high and low side gate drivers cannot be achieved without taking due considerations during circuit board layout. The following points are emphasized.

1. In order to avoid large negative transients on the switch node (HS) pin, the parasitic inductances in the source of top MOSFET and in the drain of the bottom MOSFET (synchronous rectifier) must be minimized.
2. Grounding considerations:
   - The first priority in designing grounding connections is to confine the high peak currents from charging and discharging the MOSFET gate in a minimal physical area. This will decrease the loop inductance and minimize noise issues on the gate terminal of the MOSFET. The MOSFETs should be placed as close as possible to the gate driver.
   - The second high current path includes the bootstrap capacitor, the bootstrap diode, the local ground referenced bypass capacitor and low side MOSFET body diode. The bootstrap capacitor is recharged on a cycle-by-cycle basis through the bootstrap diode from the ground referenced V_{DD} bypass capacitor. The recharging occurs in a short time interval and involves high peak current. Minimizing this loop length and area on the circuit board is important to ensure reliable operation.
3. The resistor on the RT pin must be placed very close to the IC and separated from high current paths to avoid noise coupling to the time delay generator which could disrupt timer operation.

16.2 Layout Example

Figure 22 shows an example layout for the SM74104 in the 8-pin SOIC package option.

Layout Example (continued)

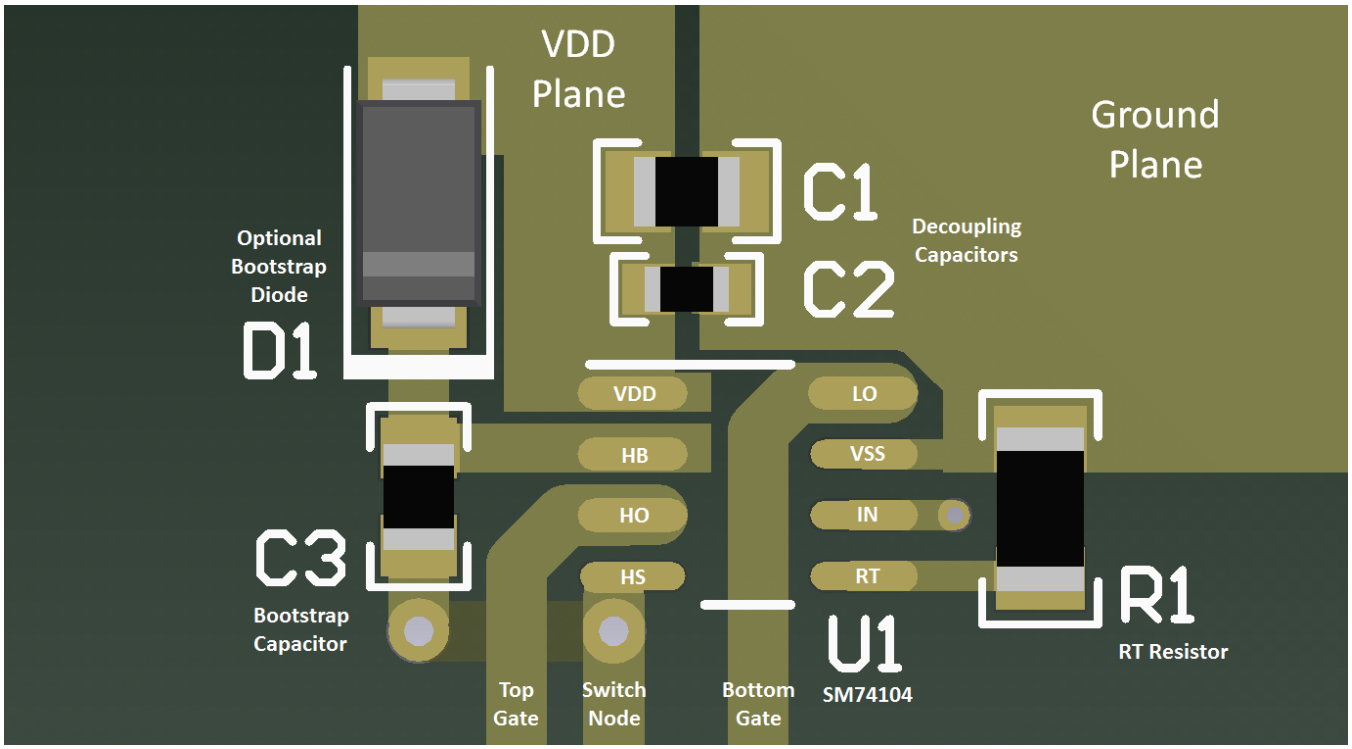


Figure 22. SM74104 Layout Example

17 Device and Documentation Support

17.1 Trademarks

All trademarks are the property of their respective owners.

17.2 Electrostatic Discharge Caution

These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

17.3 Glossary

SLYZ022 — *TI Glossary*.

This glossary lists and explains terms, acronyms, and definitions.

PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead/Ball Finish (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
SM74104MA/NOPB	ACTIVE	SOIC	D	8	95	Green (RoHS & no Sb/Br)	SN	Level-1-260C-UNLIM	-40 to 125	74104 MA	Samples
SM74104MAX/NOPB	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	SN	Level-1-260C-UNLIM	-40 to 125	74104 MA	Samples
SM74104SD/NOPB	ACTIVE	WSON	DPR	10	1000	Green (RoHS & no Sb/Br)	SN	Level-1-260C-UNLIM	-40 to 125	S74104	Samples
SM74104SDX/NOPB	ACTIVE	WSON	DPR	10	4500	Green (RoHS & no Sb/Br)	SN	Level-1-260C-UNLIM	-40 to 125	S74104	Samples

(1) The marketing status values are defined as follows:
ACTIVE: Product device recommended for new designs.
LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.
NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.
PREVIEW: Device has been announced but is not in production. Samples may or may not be available.
OBSOLETE: TI has discontinued the production of the device.

(2) **RoHS:** TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".
RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.
Green: TI defines "Green" to mean the content of Chlorine (Cl) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

(3) MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

(4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

(6) Lead/Ball Finish - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead/Ball Finish values may wrap to two lines if the finish value exceeds the maximum column width.

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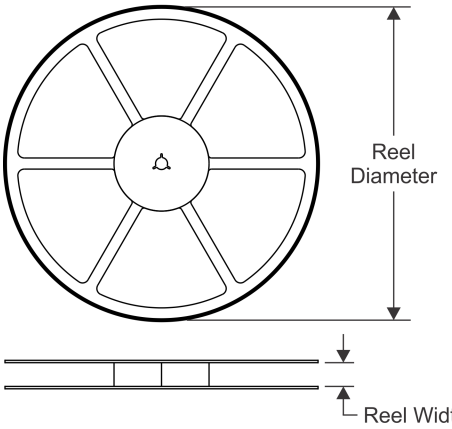
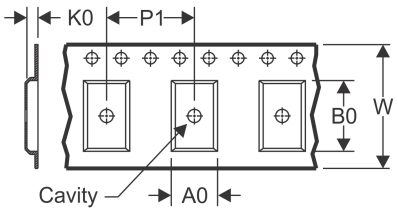
TAPE AND REEL INFORMATION

REEL DIMENSIONS

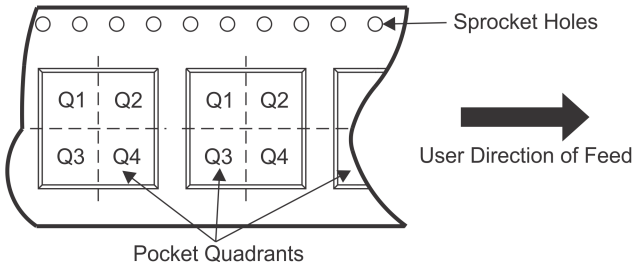


TAPE DIMENSIONS



A0	Dimension designed to accommodate the component width
B0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

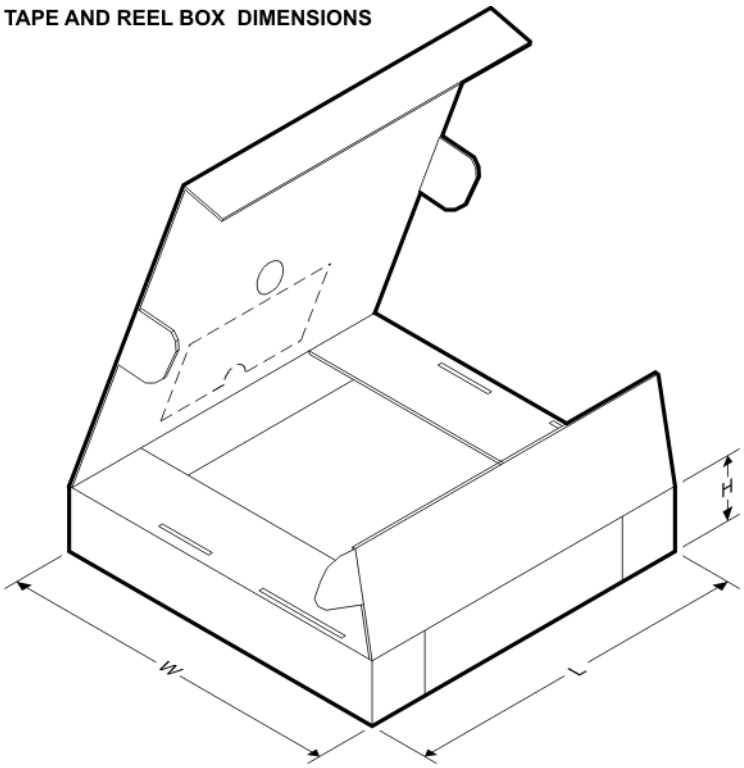
QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

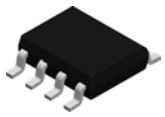
Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
SM74104MAX/NOPB	SOIC	D	8	2500	330.0	12.4	6.5	5.4	2.0	8.0	12.0	Q1
SM74104SD/NOPB	WSON	DPR	10	1000	178.0	12.4	4.3	4.3	1.3	8.0	12.0	Q1
SM74104SDX/NOPB	WSON	DPR	10	4500	330.0	12.4	4.3	4.3	1.3	8.0	12.0	Q1

TAPE AND REEL BOX DIMENSIONS



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
SM74104MAX/NOPB	SOIC	D	8	2500	367.0	367.0	35.0
SM74104SD/NOPB	WSON	DPR	10	1000	210.0	185.0	35.0
SM74104SDX/NOPB	WSON	DPR	10	4500	367.0	367.0	35.0

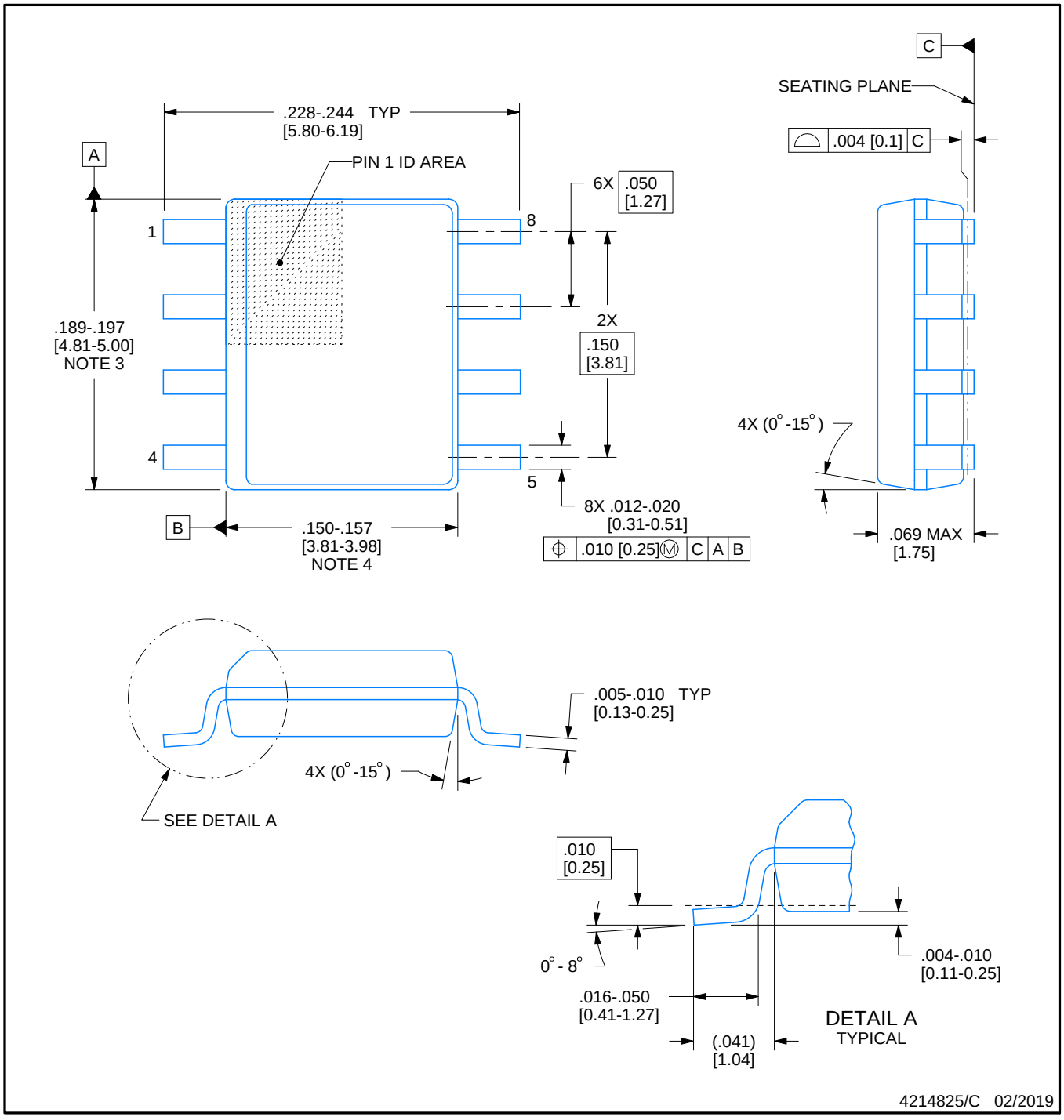


PACKAGE OUTLINE

D0008A

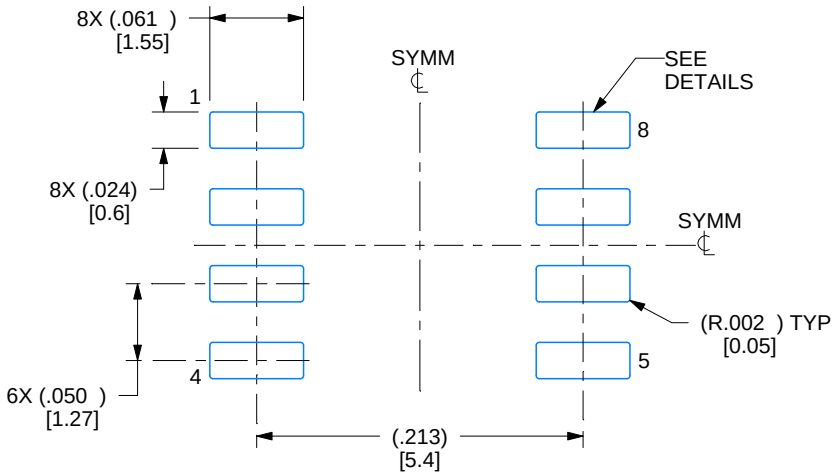
SOIC - 1.75 mm max height

SMALL OUTLINE INTEGRATED CIRCUIT

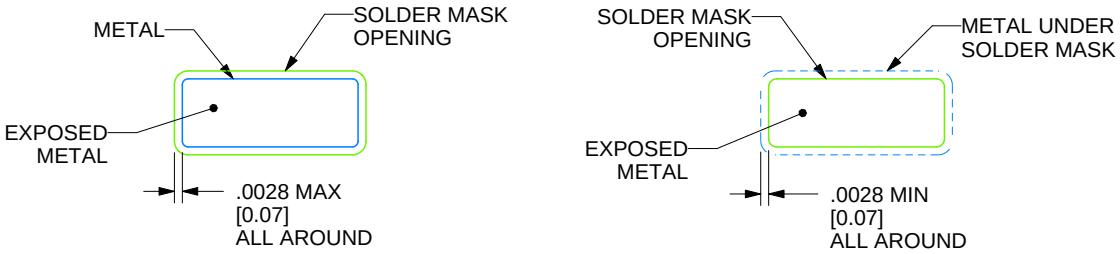


NOTES:

1. Linear dimensions are in inches [millimeters]. Dimensions in parenthesis are for reference only. Controlling dimensions are in inches. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed .006 [0.15] per side.
4. This dimension does not include interlead flash.
5. Reference JEDEC registration MS-012, variation AA.



LAND PATTERN EXAMPLE
EXPOSED METAL SHOWN
SCALE:8X



SOLDER MASK DETAILS

4214825/C 02/2019

NOTES: (continued)

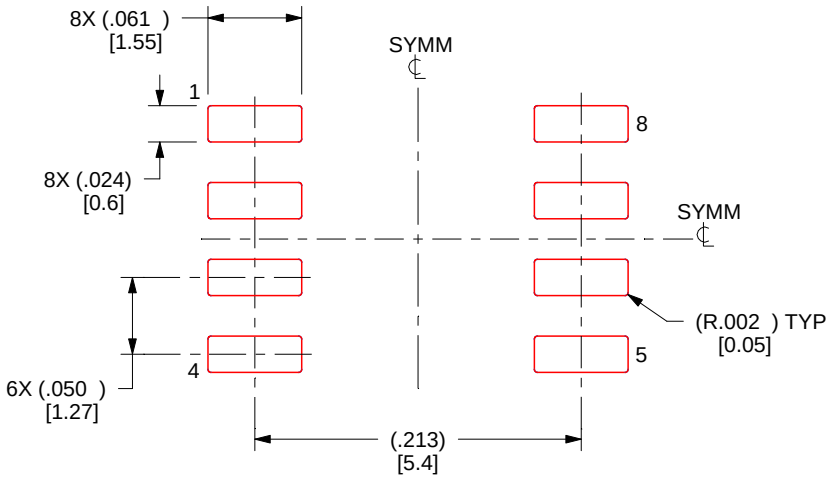
6. Publication IPC-7351 may have alternate designs.
7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.

EXAMPLE STENCIL DESIGN

D0008A

SOIC - 1.75 mm max height

SMALL OUTLINE INTEGRATED CIRCUIT



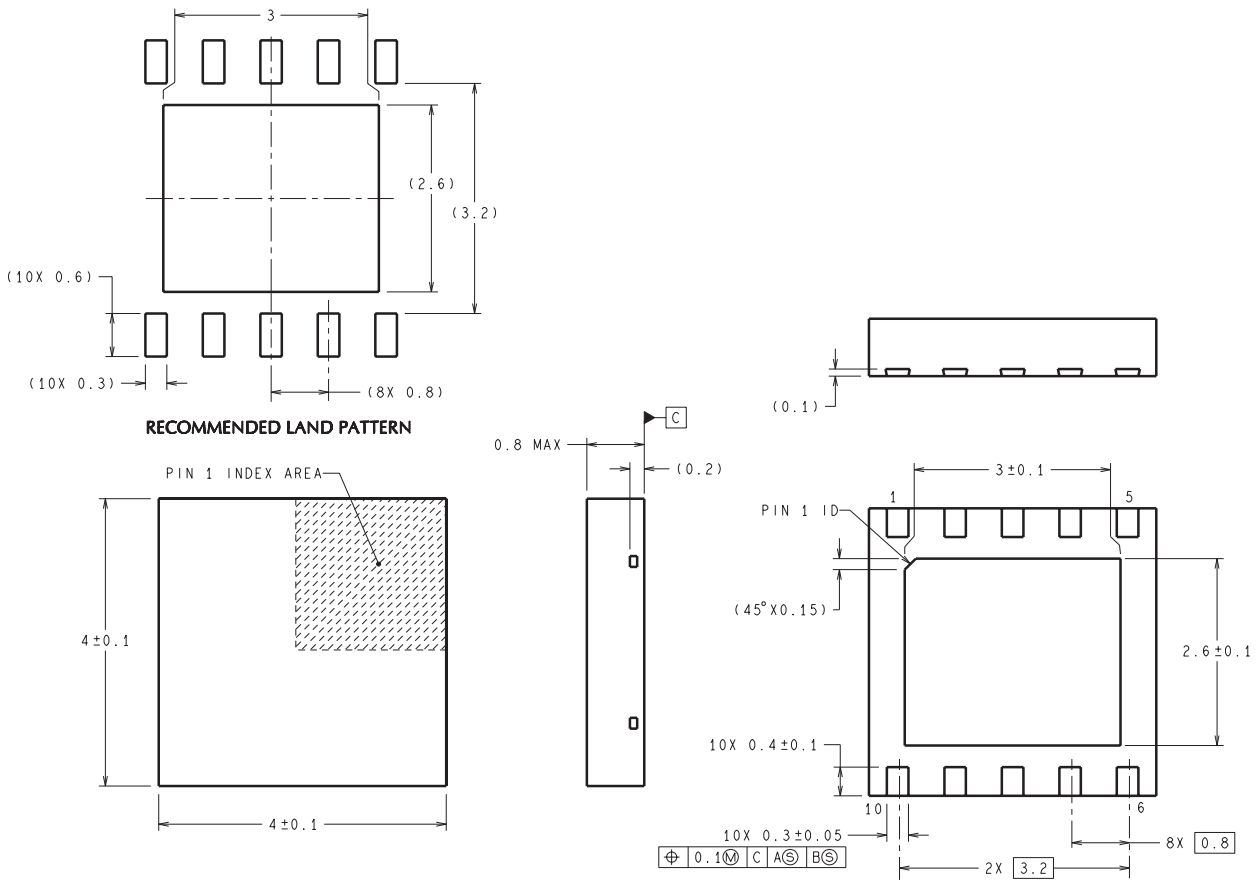
SOLDER PASTE EXAMPLE
BASED ON .005 INCH [0.125 MM] THICK STENCIL
SCALE:8X

4214825/C 02/2019

NOTES: (continued)

8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
9. Board assembly site may have different recommendations for stencil design.

DPR0010A



DIMENSIONS ARE IN MILLIMETERS

SDC10A (Rev A)

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